

FORM PTO-1449 (SUBSTITUTE)


U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEINFORMATION DISCLOSURE
STATEMENT BY APPLICANT
(37 CFR 1.98(b))Attorney Docket No.:
GR 00 P 1281Applic. No.
09/783,187

Applicant

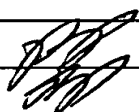
Harald Bachhofer et al.

Filing Date
February 14, 2001Group Art Unit
2822


U.S. PATENT DOCUMENTS

EXAMINER INITIALS		PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE
	A	2001/0038117 A1	11/08/01	Haneder et al.	_____	_____	
	B						
	C						
	D						
	E						
	F						
	G						
	H						
	I						

FOREIGN PATENT DOCUMENT

		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES NO
	J	198 40 824 C1	10/21/99	Germany	_____	_____	X
	K	WO 92/12518	07/23/92	WIPO	_____	_____	X
	L						
	M						
	N						

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

	O	
	P	
EXAMINER		
	DATE CONSIDERED 5/3/03	

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609;
Draw line through citation if not in conformance and not considered. Include copy of this form with
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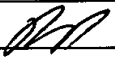
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U.S. PATENT DOCUMENTS

EXAMINER INITIALS		PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE
	A	5,946,224	08/31/99	Nishimura	—	—	
	B						
	C						
	D						
	E						
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FOREIGN PATENT DOCUMENT

		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES NO
	J						
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

	O	Takashi Nakamura et al.: "A Single-Transistor Ferroelectric Memory Cell", 1995 IEEE International Solid-State Circuits Conference, pp. 68-69
	P	Jong-Son Lyu et al.: "Metal-Ferroelectric-Semiconductor Field-Effect Transistor (MFSFET) for Single Transistor Memory by Using Poly-Si Source/Drain and BaMgF ₄ Dielectric", IEDM 1996, pp. 503-506

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